


[Home](#) | [Login](#) | [Logout](#) | [Access Information](#) |

Welcome United States Patent and Trademark Office
 Search Results

Results for "((plasma and antenna and ratio and mos and capacit*)<in>metadata)"

Your search matched **8** of **1322957** documents.

A maximum of **100** results are displayed, **25** to a page, sorted by **Relevance in Descending order.**
[BROWSE](#)[SEARCH](#)[IEEE XPLORE GUIDE](#)
» Search Options
[View Session History](#)
[New Search](#)
» Key
IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

Modify Search

 Check to search only within this results set

Display Format:
 Citation

 Citation & Abstract

[view selected items](#)
[Select All](#) [Deselect All](#)

- 1. Plasma-induced charging damage to MOS capacitor structures in cyclotron-resonance plasmas**
Friedmann, J.B.; Ma, S.-M.; McVittie, J.P.; Shohet, J.L.;
Plasma Science, 1995. IEEE Conference Record - Abstracts., 1995 International Conference on
5-8 June 1995 Page(s):164
Digital Object Identifier 10.1109/PLASMA.1995.531626
[AbstractPlus](#) | [Full Text: PDF\(112 KB\)](#) [IEEE CNF Rights and Permissions](#)
- 2. Prediction of plasma charging induced gate oxide damage by probe**
Shawming Ma; McVittie, J.P.; Saraswat, K.C.;
Electron Device Letters, IEEE
Volume 18, Issue 10, Oct. 1997 Page(s):468 - 470
Digital Object Identifier 10.1109/55.624913
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(84 KB\)](#) [IEEE JNL Rights and Permissions](#)
- 3. Evaluation of charge build-up in wafer processing by using with charge collecting electrodes**
Kubo, H.; Namura, T.; Yoneda, K.; Ohishi, H.; Todokoro, Y.;
Microelectronic Test Structures, 1995. ICMTS 1995. Proceeding: International Conference on
22-25 March 1995 Page(s):5 - 9
Digital Object Identifier 10.1109/ICMTS.1995.513936
[AbstractPlus](#) | [Full Text: PDF\(480 KB\)](#) [IEEE CNF Rights and Permissions](#)
- 4. Resist-related damage on ultrathin gate oxide during plasma**
Chao-Hsin Chien; Chun-Yen Chang; Horng-Chih Lin; Tsai-Fu Chiou; Liang-Po Chen; Tiao-Yuan Huang;
Electron Device Letters, IEEE
Volume 18, Issue 2, Feb. 1997 Page(s):33 - 35
Digital Object Identifier 10.1109/55.553034
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(64 KB\)](#) [IEEE JNL Rights and Permissions](#)

- 5. Reduction and non-uniformity of high density plasma process electrical degradation in MOS devices
Pei-Jer Tzeng; Jen-Chieh Li; Chun-Chen Yeh; Kuei-Shu Chang-I
Plasma Process-Induced Damage, 1999 4th International Symposium
9-11 May 1999 Page(s):100 - 103
Digital Object Identifier 10.1109/PPID.1999.798823
[AbstractPlus](#) | [Full Text: PDF\(188 KB\)](#) | [IEEE CNF](#)
[Rights and Permissions](#)

- 6. The role of resist for ultrathin gate oxide degradation during Chao-Hsin Chien; Chun-Yen Chang; Horng-Chih Lin; Shean-Gu; Yuan Huang; Tsai-Fu Chang; Szu-Kang Hsien;
Electron Device Letters, IEEE
Volume 18, Issue 5, May 1997 Page(s):203 - 205
Digital Object Identifier 10.1109/55.568764
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(60 KB\)](#) | [IEEE JNL](#)
[Rights and Permissions](#)

- 7. Sensitivity and limitations of plasma charging damage measurement in MOS capacitors structures
Shawming Ma; Abdel-Ati, W.L.N.; McVittie, P.;
Electron Device Letters, IEEE
Volume 18, Issue 9, Sept. 1997 Page(s):420 - 422
Digital Object Identifier 10.1109/55.622516
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(88 KB\)](#) | [IEEE JNL](#)
[Rights and Permissions](#)

- 8. A study of wafer charging with CHARM-2 and large area capacitors Current, M.I.; de Haan, S.;
Ion Implantation Technology. Proceedings of the 11th International Conference
16-21 June 1996 Page(s):65 - 68
Digital Object Identifier 10.1109/IIT.1996.586125
[AbstractPlus](#) | [Full Text: PDF\(264 KB\)](#) | [IEEE CNF](#)
[Rights and Permissions](#)

[Help](#) | [C](#)